
IN THE SPECIFICATION

Please amend the specification paragraph beginning at page 1, line 5, as follows:

Q1 This application is related to the following co-pending, commonly assigned U.S. patent applications: "DRAM Cells with Repressed Memory Metal Oxide Tunnel Insulators," attorney docket no. 1303.019US1, ~~serial number~~ serial number 09/945,395, "Programmable Array Logic or Memory Devices with Asymmetrical Tunnel Barriers," attorney docket no. 1303.020US1, ~~serial number~~ serial number 09/943,134, "Dynamic Electrically Alterable Programmable Memory with Insulating Metal Oxide Interpoly Insulators," attorney docket no. 1303.024US1, ~~serial number~~ serial number 09/945,498, and "Flash Memory with Low Tunnel Barrier Interpoly Insulators," attorney docket no. 1303.014US1, ~~serial number~~ serial number 09/945,507, "SRAM Cells with Repressed Floating Gate Memory, Metal Oxide Tunnel Interpoly Insulators," attorney docket no. 1303.028US1, ~~serial number~~ serial number 09/945,554, "~~Flash Memory with Low Tunnel Barrier Interpoly Insulators,~~" ~~attorney docket no. 1303.014US1,~~ ~~serial number~~, which are filed on even date herewith and each of which disclosure is herein incorporated by reference

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